

*Status of the Claims*

The listing of claims will replace all prior versions, and listings of claims in the application.

1. (original) A metal-insulator-metal (MIM) capacitor process, comprising:  
forming a first metal layer on a substrate, wherein a portion of the first metal layer is utilized as the lower plate of the MIM capacitor;  
forming an etch stop layer on the substrate and the first metal layer, wherein a portion of an etch stop layer is utilized as the insulator for the MIM capacitor;  
and  
forming a second metal layer on the substrate and portion of an etch stop layer, wherein a portion of the second metal layer is utilized as the upper plate of the MIM capacitor;  
wherein the first and the second metal layers include copper or a copper alloy.
2. (original) The process according to claim 1, wherein the stop layer includes a silicon nitride layer.
3. (original) The process according to claim 1, wherein the second metal layer is polished by chemical-mechanical polishing.
4. (original) The process according to claim 1, wherein the first metal layer is polishing by chemical-mechanical polishing.